



Attorney's Docket No.: 10559-587001 / P12768

2821
Hw

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Been-Yih Jin et al. Art Unit : 2812
Serial No. : 10/081,992 Examiner : Ron Everett Pompey
Filed : February 21, 2002
Title : NON-SILICON SEMICONDUCTOR AND HIGH-K GATE DIELECTRIC
METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Mail Stop AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT IN REPLY TO ACTION OF SEPTEMBER 22, 2004

Please amend the above-identified application as follows:

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

12/2/04
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